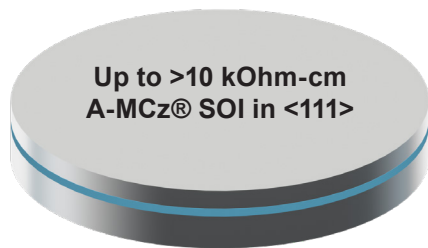




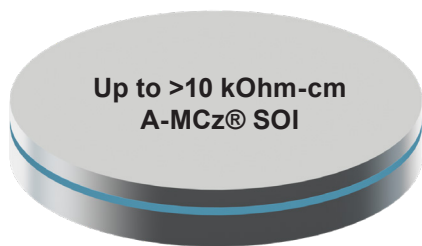
RF GaN Substrate Wafers

Si and SOI wafers



- RF GaN Substrate wafers are designed to endure the extreme stresses of the epi process and to minimize the insertion losses
- Typically extra thick <111> MCz grown Si and SOI wafers with advanced stress management to reduce wafer bow and warpage
- Up to >10 kOhm-cm resistivity with suitable Oi control, optimal balance between resistivity stability, lattice integrity and durability.
- Engineered edges optimize gas flow and thermal distribution for consistent processing
- Available in 150-200 mm

High Resistivity SOI Wafers



- High Resistivity Bonded Silicon-On-Insulator wafers with suspended low-loss structures enable lumped element solutions combined with novel approaches such as stripline filters
- Low-loss device layer material can also be combined with turnkey Cavity SOI structures (C-SOI®) to create a platform for new type of BAW resonators or IPD devices
- Manufactured with Advanced Magnetic Czochralski (A-MCz®) crystal growth method enabling low Oi and very high resistivities of >10 kOhm-cm (BSOI) and >7 kOhm-cm (C-SOI®)
- Available in 150-200 mm